

PROCEEDINGS OF SPIE

***Photomask Japan 2018: XXV
Symposium on Photomask and
Next-Generation Lithography Mask
Technology***

Kiwamu Takehisa
Editor

18–20 April 2018
Yokohama, Japan

Organized by
Photomask Japan
SPIE

Co-organized by
BACUS
EMLC

In Cooperation with
The Japan Society of Applied Physics
The Japan Society for Precision Engineering
The Institute of Electrical Engineering (Japan)
Technical Exhibit in Cooperation with SEMI (Japan)

Supported by
City of Yokohama

Published by
SPIE

Volume 10807

Proceedings of SPIE 0277-786X, V. 10807

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

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Author(s), "Title of Paper," in *Photomask Japan 2018: XXV Symposium on Photomask and Next-Generation Lithography Mask Technology*, edited by Kiwamu Takehisa, Proceedings of SPIE Vol. 10807 (SPIE, Bellingham, WA, 2018) Seven-digit Article CID Number.

ISSN: 0277-786X

ISSN: 1996-756X (electronic)

ISBN: 9781510622012

ISBN: 9781510622029 (electronic)

Published by

SPIE

P.O. Box 10, Bellingham, Washington 98227-0010 USA

Telephone +1 360 676 3290 (Pacific Time) Fax +1 360 647 1445

SPIE.org

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Printed in the United States of America

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